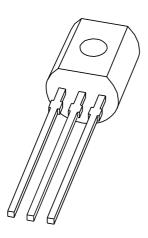
DISCRETE SEMICONDUCTORS

DATA SHEET



MPS3904 NPN switching transistor

Product specification Supersedes data of 1999 Apr 12 2004 Oct 11





NPN switching transistor

MPS3904

FEATURES

- Low current (max. 100 mA)
- Low voltage (max. 40 V).

APPLICATIONS

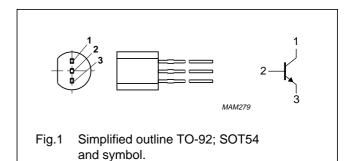
• General purpose switching and amplification.

DESCRIPTION

NPN transistor in a TO-92; SOT54 plastic package. PNP complement: MPS3906.

PINNING

PIN	DESCRIPTION
1	collector
2	base
3	emitter



ORDERING INFORMATION

TYPE NUMBER		PACKAGE					
ITPE NOWIBER	NAME DESCRIPTION VERSI						
MPS3904	SC-43A	plastic single-ended leaded (through hole) package; 3 leads					

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	_	60	V
V _{CEO}	collector-emitter voltage	open base	_	40	V
V _{EBO}	emitter-base voltage	open collector	_	6	V
I _C	collector current (DC)		_	100	mA
I _{CM}	peak collector current		_	200	mA
I _{BM}	peak base current		_	200	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	_	500	mW
T _{stg}	storage temperature		-65	+150	°C
T _j	junction temperature		_	150	°C
T _{amb}	ambient temperature		-65	+150	°C

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th(j-a)}	thermal resistance from junction to ambient	note 1	250	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I _{CBO}	collector-base cut-off current	V _{CB} = 30 V; I _E = 0 A	-	50	nA
I _{EBO}	emitter-base cut-off current	V _{EB} = 5 V; I _C = 0 A	_	50	nA
h _{FE}	DC current gain	V _{CE} = 1 V; note 1			
		I _C = 0.1 mA	40	_	
		I _C = 1 mA	70	_	
		I _C = 10 mA	100	300	
		I _C = 50 mA	60	_	
		I _C = 100 mA	30	_	
V _{CEsat}	collector-emitter saturation voltage	I _C = 10 mA; I _B = 1 mA; note 1	_	200	mV
		$I_C = 50 \text{ mA}; I_B = 5 \text{ mA}; \text{ note 1}$	_	300	mV
V _{BEsat}	base-emitter saturation voltage	I _C = 10 mA; I _B = 1 mA; note 1	650	850	mV
		I _C = 50 mA; I _B = 5 mA; note 1	_	950	mV
C _c	collector capacitance	$V_{CB} = 5 \text{ V}; I_E = i_e = 0 \text{ A};$ f = 100 kHz to 1 MHz	_	5	pF
C _e	emitter capacitance	$V_{EB} = 0.5 \text{ V}; I_C = I_c = 0 \text{ A};$ f = 100 kHz to 1 MHz	_	15	pF
f _T	transition frequency	V _{CE} = 20 V; I _C = 10 mA; f = 100 MHz	180	_	MHz
F	noise figure	V_{CE} = 5 V; I_{C} = 100 μA; R_{S} = 1 kΩ; f = 10 Hz to 15.7 kHz	_	5	dB
Switching t	times (between 10 % and 90 % levels	s); (see Fig.2)	•		•
t _{on}	turn-on time	$I_{Con} = 10 \text{ mA}; I_{Bon} = 1 \text{ mA}; I_{Boff} = -1 \text{ mA};$	_	110	ns
t _d	delay time	$V_{CC} = 3 \text{ V}; V_{BB} = -1.9 \text{ V}$	_	50	ns
t _r	rise time	1	_	60	ns
t _{off}	turn-off time	1	_	1200	ns
t _s	storage time	1	_	1000	ns
t _f	fall time	1	_	200	ns

Note

1. Pulse test: $t_p \le 300 \ \mu s; \ \delta = 0.02.$

NPN switching transistor

Oscilloscope: input impedance $Z_i = 50 \ \Omega$.

MPS3904

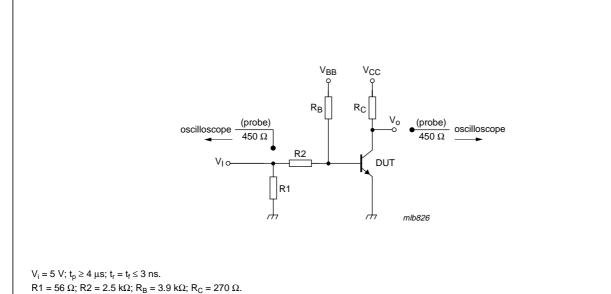


Fig.2 Test circuit for switching times.

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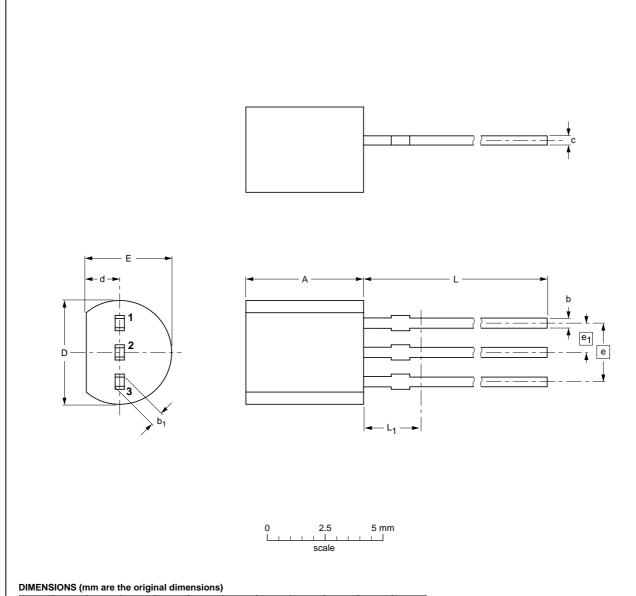
NPN switching transistor

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PACKAGE OUTLINE

Plastic single-ended leaded (through hole) package; 3 leads

SOT54



UNIT	A	b	b ₁	С	D	d	E	е	e ₁	L	L ₁ ⁽¹⁾ max.	
mm	5.2 5.0	0.48 0.40	0.66 0.55	0.45 0.38	4.8 4.4	1.7 1.4	4.2 3.6	2.54	1.27	14.5 12.7	2.5	

Note

1. Terminal dimensions within this zone are uncontrolled to allow for flow of plastic and terminal irregularities.

OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE
SOT54		TO-92	SC-43A		97-02-28 04-06-28

NPN switching transistor

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DATA SHEET STATUS

LEVEL	DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS(2)(3)	DEFINITION
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Printed in The Netherlands

R75/04/pp7

Date of release: 2004 Oct 11

Document order number: 9397 750 13607

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